

Accepted Manuscript

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Authors: Mingzeng Peng, Xinhe Zheng, Ziguang Ma, Hong Chen, Sanjie Liu, Yingfeng He, Meiling Li



PII: S0925-4005(17)31977-9
DOI: <https://doi.org/10.1016/j.snb.2017.10.077>
Reference: SNB 23381

To appear in: *Sensors and Actuators B*

Received date: 11-5-2017
Revised date: 12-10-2017
Accepted date: 14-10-2017

Please cite this article as: Mingzeng Peng, Xinhe Zheng, Ziguang Ma, Hong Chen, Sanjie Liu, Yingfeng He, Meiling Li, Ni-pattern guided GaN nanowire-array humidity sensor with high sensitivity enhanced by UV photoexcitation, *Sensors and Actuators B: Chemical* <https://doi.org/10.1016/j.snb.2017.10.077>

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Ni-pattern guided GaN nanowire-array humidity sensor with high sensitivity enhanced by UV photoexcitation

Mingzeng Peng,^{1,3*} Xinhe Zheng,^{1,3} Ziguang Ma,² Hong Chen,² Sanjie Liu,^{1,3} Yingfeng He,^{1,3}
Meiling Li^{1,3}

¹ School of Mathematics and Physics, University of Science and Technology Beijing, No. 30, Xueyuan Road, Beijing 100083, China

² Beijing National Laboratory for Condensed Matter Physics, Institute of Physics, Chinese Academy of Sciences, Beijing 100190, China

³ Beijing Key Laboratory for Magneto-Photoelectrical Composite and Interface Science, University of Science and Technology Beijing, No. 30, Xueyuan Road, Beijing 100083, China

*Address correspondence to mzpeng@ustb.edu.cn (MZP)

Highlights

- We have proposed a simple Ni-pattern guided lateral growth method to fabricate selective-area GaN nanowire array.
- Ni metal has formed contamination-free and high-quality Schottky-contacted interface with in-situ grown GaN nanowire array.
- In the RH range from 15 % to 85 %, its output current has a sharp decrease from 29.3 to 0.913 μA and from -16.8 to -0.215 μA when biased at 5 and -5 V respectively, exhibiting its ultrahigh RH sensing above two orders of magnitude.
- Its RH sensitivity has been largely enhanced by UV photoexcitation from 3208 % to 10066 % at 5 V and from 7818 % to 24037 % at -5 V, respectively.

ABSTRACT

Selective-area lateral GaN nanowire array has been one-step fabricated over large scale by Ni-pattern guided chemical vapor deposition (CVD) growth. Two neighboring Ni electrodes, acting as source and drain, can be bridged across by a

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